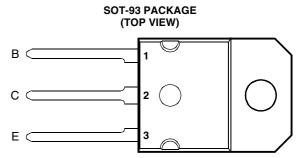
# **BOURNS®**

- Designed for Complementary Use with the BD249 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

1

# absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BD250		-55		
Collector-emitter voltage ( $R_{BE} = 100 \Omega$ )	BD250A	V	-70	V	
Collector Chillian Actual (LIBE - 100 35)	BD250B	V <sub>CER</sub>	-90	٧	
	BD250C		-115		
	BD250		-45		
Collector-emitter voltage (I <sub>C</sub> = -30 mA)	BD250A	V	-60	V	
Collector-entitles voltage (IC = -30 IIIA)	BD250B	V <sub>CEO</sub>	-80	V	
	BD250C		-100		
Emitter-base voltage			-5	V	
Continuous collector current			-25	Α	
Peak collector current (see Note 1)			-40	Α	
Continuous base current			-5	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			125	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			3	W	
Unclamped inductive load energy (see Note 4)			90	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			T <sub>L</sub> 250		

NOTES: 1. This value applies for  $t_p \le 0.3$  ms, duty cycle  $\le 10\%$ .

- 2. Derate linearly to  $150^{\circ}$ C case temperature at the rate of 1 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH,  $I_{B(on)}$  = -0.4 A,  $R_{BE}$  = 100  $\Omega$ ,  $V_{BE(off)}$  = 0,  $R_S$  = 0.1  $\Omega$ ,  $V_{CC}$  = -20 V.



# electrical characteristics at 25°C case temperature

	PARAMETER		TEST CONDITIO	DNS	MIN	TYP	MAX	UNIT	
	Collector-emitter			BD250 BD250A	-45 -60				
V <sub>(BR)CEO</sub>	breakdown voltage	$I_C = -30 \text{ mA}$	$I_B = 0$	BD250B	-80			V	
		(see Note 5)		BD250C	-100				
		V <sub>CE</sub> = -55 V	$V_{BE} = 0$	BD250			-0.7		
1	Collector-emitter	$V_{CE} = -70 \text{ V}$	$V_{BE} = 0$	BD250A			-0.7	mA	
ICES	cut-off current	$V_{CE} = -90 V$	$V_{BE} = 0$	BD250B			-0.7	ША	
		V <sub>CE</sub> = -115 V	$V_{BE} = 0$	BD250C			-0.7		
1	Collector cut-off	$V_{CE} = -30 \text{ V}$	I <sub>B</sub> = 0	BD250/250A			-1	mA	
ICEO	current	$V_{CE} = -60 \text{ V}$	$I_B = 0$	BD250B/250C			-1	"	
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = -5 V	I <sub>C</sub> = 0				-1	mA	
	Forward current	V <sub>CE</sub> = -4 V	I <sub>C</sub> = -1.5 A		25				
h <sub>FE</sub>	transfer ratio	transfer ratio	$V_{CE} = -4 V$	$I_{C} = -15 A$	(see Notes 5 and 6)	10			
		$V_{CE} = -4 V$	-		5				
V <sub>CE(sat)</sub>	Collector-emitter	I <sub>B</sub> = -1.5 A	$I_{\rm C} = -15  {\rm A}$	(see Notes 5 and 6)			-1.8	V	
* CE(sat)	saturation voltage	I <sub>B</sub> = -5 A	-				-4	•	
V <sub>BE</sub>	Base-emitter	V <sub>CE</sub> = -4 V	I <sub>C</sub> = -15 A	(see Notes 5 and 6)			-2	٧	
*BE	voltage	$V_{CE} = -4 V$	$I_C = -25 A$				-4	•	
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = -1A	f = 1 kHz	25				
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = -1 A	f = 1 MHz	3				

NOTES: 5. These parameters must be measured using pulse techniques,  $t_p$  = 300  $\mu$ s, duty cycle  $\leq$  2%.

### thermal characteristics

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1	°C/W
$R_{\theta,JA}$	Junction to free air thermal resistance			42	°C/W

# resistive-load-switching characteristics at 25°C case temperature

		PARAMETER	TEST CONDITIONS †		MIN	TYP	MAX	UNIT	
Γ	t <sub>on</sub>	Turn-on time	I <sub>C</sub> = -5 A	$I_{B(on)} = -0.5 A$	$I_{B(off)} = 0.5 A$		0.2		μs
	t <sub>off</sub>	Turn-off time	$V_{BF(off)} = 5 V$	$R_1 = 5 \Omega$	$t_{\rm p} = 20 \ \mu s, \ dc \le 2\%$		0.4		μs

<sup>&</sup>lt;sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

<sup>6.</sup> These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

### **TYPICAL CHARACTERISTICS**

# TYPICAL DC CURRENT GAIN VS COLLECTOR CURRENT TCS636AD TCS636AD

Figure 1.

# **COLLECTOR-EMITTER SATURATION VOLTAGE** vs **BASE CURRENT** TCS636AB -10 V<sub>CE(sat)</sub> - Collector-Emitter Saturation Voltage - V -1.0 -0.1 300 mA -1 A -3 A -0.01 -0.01 -0.001 -0.1 -1.0 -10 -100 I<sub>B</sub> - Base Current - A

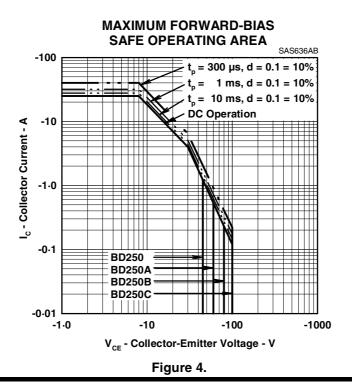
Figure 2.

# **BASE-EMITTER VOLTAGE COLLECTOR CURRENT** TCS636AC -1.8 $V_{CE} = -4 V$ $T_{\rm C} = 25^{\circ}{\rm C}$ -1.6 V<sub>BE</sub> - Base-Emitter Voltage - V -1.4 -1.2 -1.0 -0.8 -0.6 -0.1 -10 -100 I<sub>c</sub> - Collector Current - A

Figure 3.

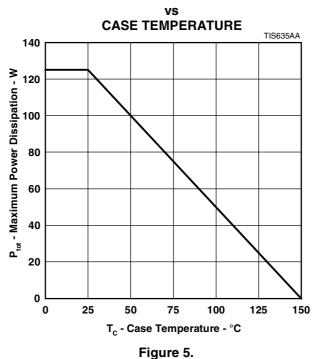
### PRODUCT INFORMATION

### **MAXIMUM SAFE OPERATING REGIONS**



### THERMAL INFORMATION

### **MAXIMUM POWER DISSIPATION**



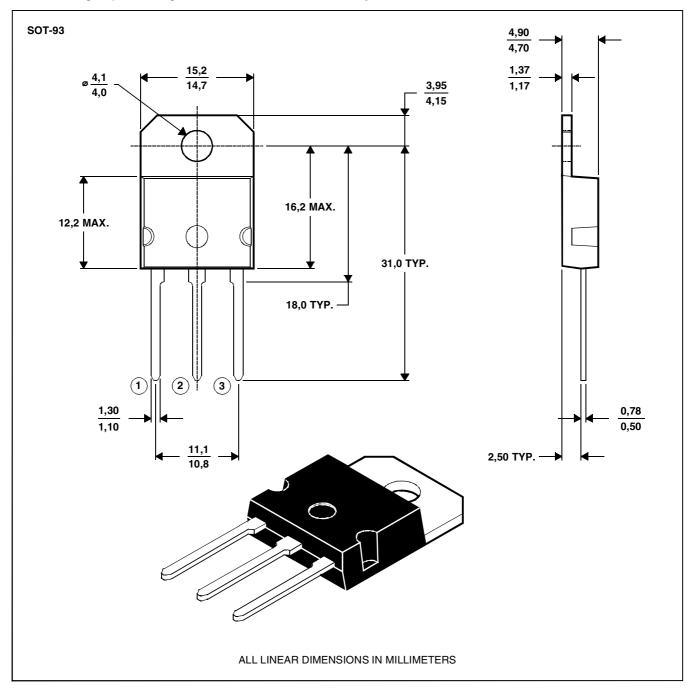
## PRODUCT INFORMATION

### **MECHANICAL DATA**

### **SOT-93**

# 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

**MDXXAW**